

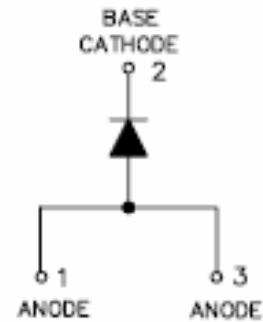
MBRD660 SCHOTTKY RECTIFIER

Applications:

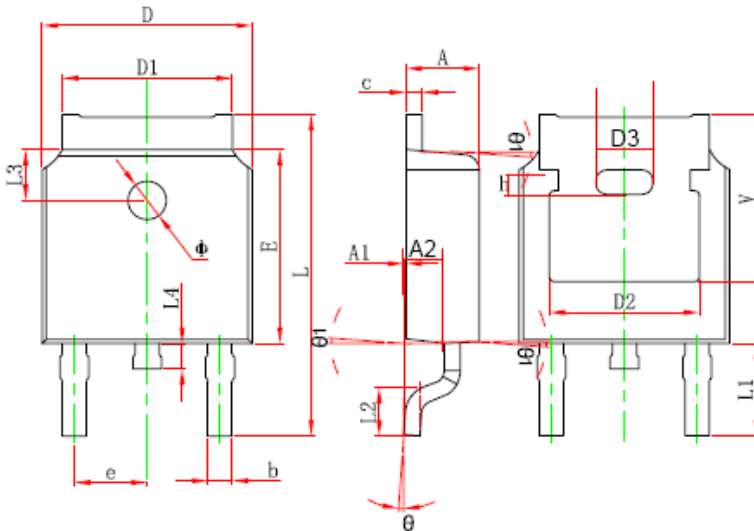
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Dimensions: In Inches / mm



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
A2	0.910	1.110	0.036	0.044
V	5.350 REF.		0.211 REF.	
D3	1.778 REF.		0.070 REF.	
h	0.762 REF.		0.030 REF.	
θ1	7°		7°	

DPAK

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
D = Package type
6 = Forward Current (6A)
60 = Reverse Voltage (60V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRD660	DDPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 85^\circ\text{C}$, rectangular wave form	6	A
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	125	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 6A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.75	V
	V_{F1}	@ 6A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.70	V
Max. Reverse Current at DC condition	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1	mA
Max. Reverse Current	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	10	mA
Max. Junction Capacitance	C_T	@ $V_R = 5.0\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	400	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	T_J	-	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	6.0	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

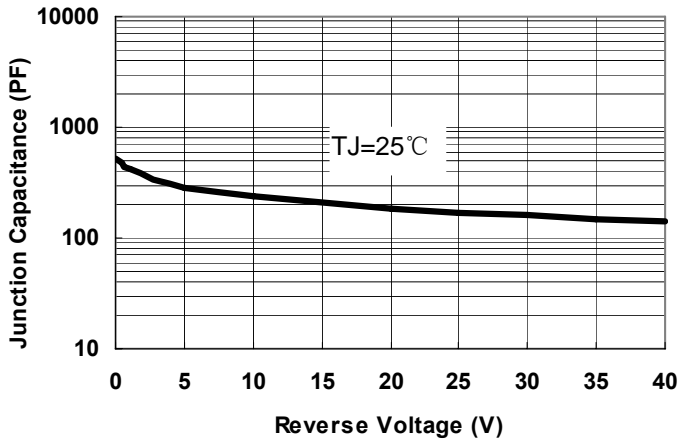


Fig.1-Typical Junction Capacitance

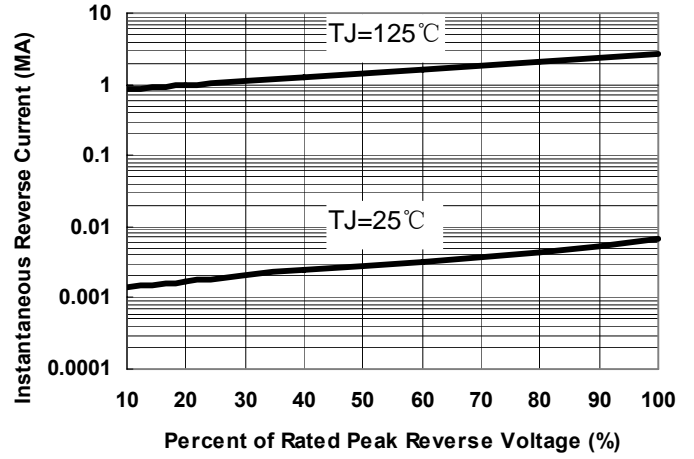


Fig.2-Typical Reverse Characteristics

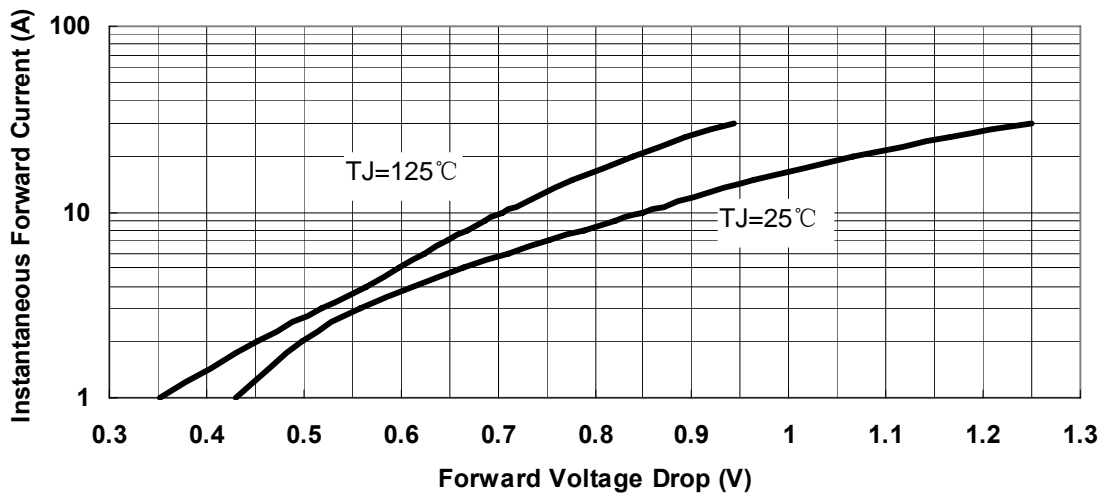


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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